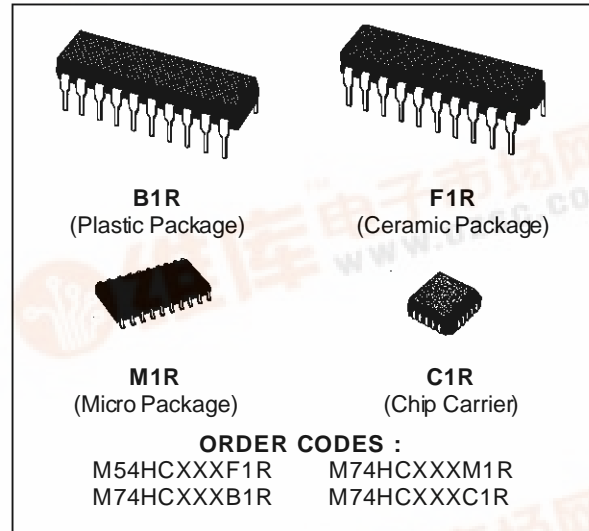




M54/74HC620 M54/74HC623

OCTAL BUS TRANSCEIVER HC620 3 STATE INVERTING HC623 3 STATE NON INVERTING

- HIGH SPEED
 $t_{PD} = 10 \text{ ns (TYP.) AT } V_{CC} = 5 \text{ V}$
- LOW POWER DISSIPATION
 $I_{CC} = 4 \mu\text{A (MAX.) AT } T_A = 25 \text{ }^\circ\text{C}$
- HIGH NOISE IMMUNITY
 $V_{NIH} = V_{NIL} = 28 \% V_{CC} \text{ (MIN.)}$
- OUTPUT DRIVE CAPABILITY
15 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE
 $|I_{OH}| = I_{OL} = 6 \text{ mA (MIN.)}$
- BALANCED PROPAGATION DELAYS
 $t_{PLH} = t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE
 $V_{CC} \text{ (OPR)} = 2 \text{ V to } 6 \text{ V}$
- PIN AND FUNCTION COMPATIBLE
WITH LS620/623



DESCRIPTION

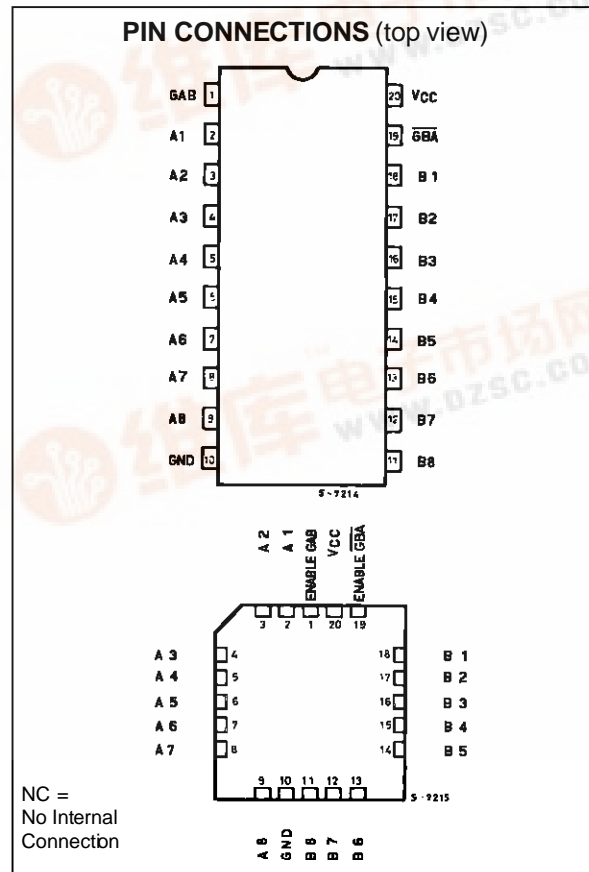
The M54/74HC620/623 are high speed CMOS OCTAL BUS TRANSCEIVERS fabricated in silicon gate C²MOS technology. They have the same high speed performance of LSTTL combined with true CMOS low power consumption.

These octal bus transceivers are designed for asynchronous two-way communication between data buses. The control function implementation allows maximum flexibility in timing.

These devices allow data transmission from the A bus to B bus or from the B to the A bus depending upon the logic levels at the enable inputs (GBA and GAB). The enable inputs can be used to disable the device so that the buses are effectively isolated.

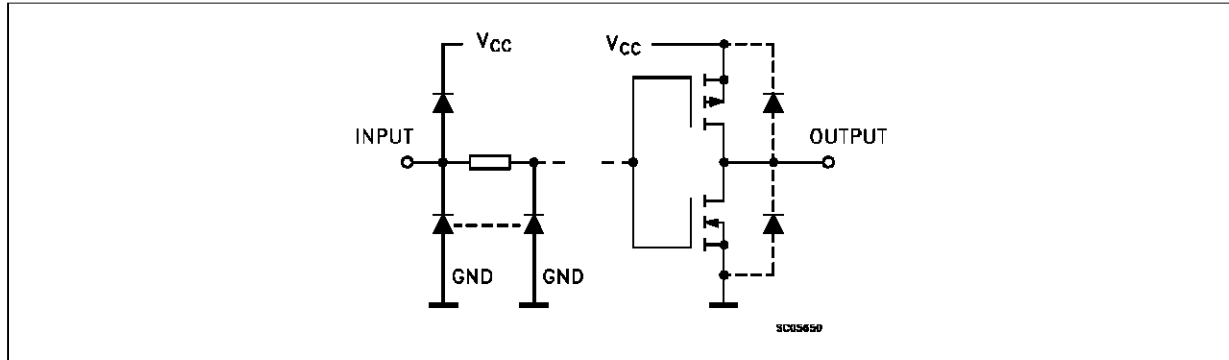
The dual-enable configuration gives these devices the capability to store data by simultaneous enabling of GBA and GAB.

Each output reinforces its input in this transceiver configuration. Thus, when both control inputs are enabled and all other data sources to the two sets of bus lines are at high impedance, both sets of bus lines (16 in all) will remain at their last states. The 8-bit codes appearing on the two sets of buses will be identical for the 'HC623 or complementary for the 'HC620. All inputs are equipped with protection circuits against static discharge and transient excess voltage.



M54/M74HC620/623

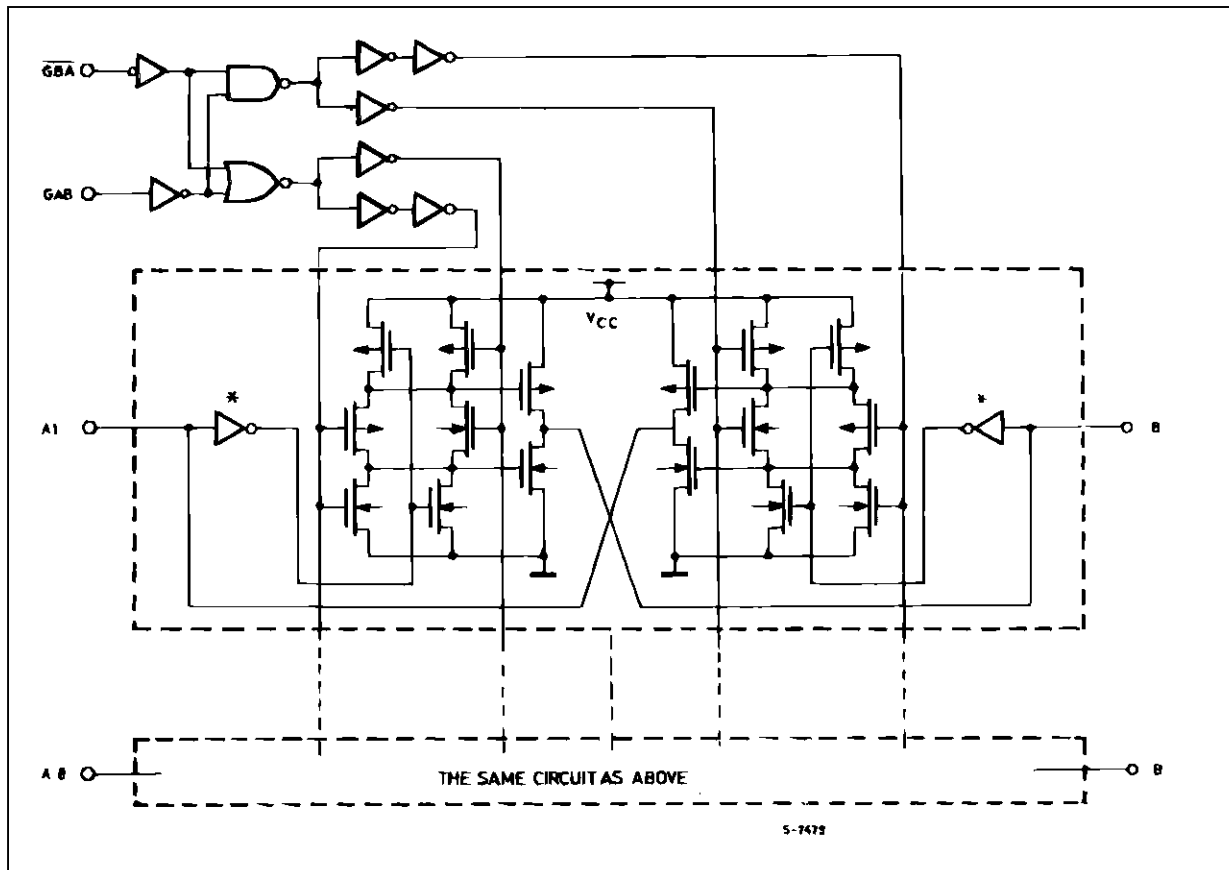
INPUT AND OUTPUT EQUIVALENT CIRCUIT



TRUTH TABLE

INPUTS		FUNCTION		OUTPUTS	
GAB	\overline{GAB}	A Bus	B Bus	HC620	HC623
L	L	Output	Input	$A = \overline{B}$	$A = B$
H	H	Input	Output	$B = \overline{A}$	$B = A$
L	H	High Impedance		Z	Z
H	L	High Impedance		Z	Z

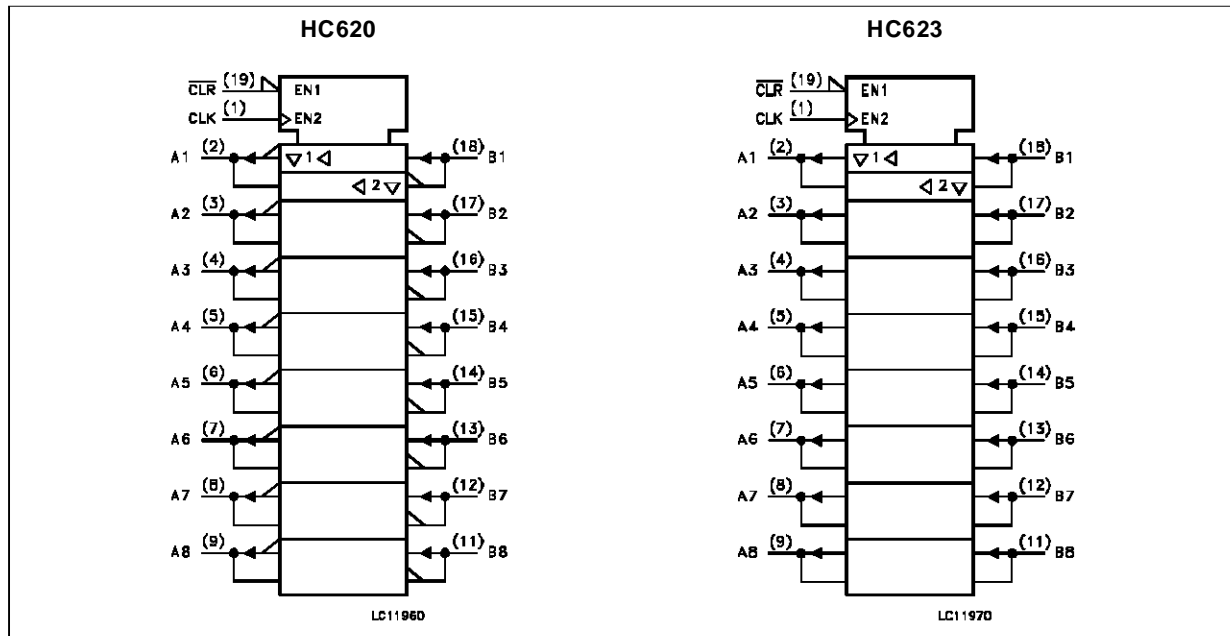
LOGIC DIAGRAM



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 19	$\overline{\text{GBA}}$, GAB	Direction Controls
2, 3, 4, 5, 6, 7, 8, 9	A1 to A8	Data Inputs/Outputs
11, 12, 13, 14, 15, 16, 17, 18	B1 to B8	Data Inputs/Outputs
10	GND	Ground (0V)
20	V _{CC}	Positive Supply Voltage

IEC LOGIC SYMBOLS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Source Sink Current Per Output Pin	± 35	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 70	mA
P _D	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(*) 500 mW: ≅ 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

M54/M74HC620/623

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V_{CC}	Supply Voltage	2 to 6	V	
V_I	Input Voltage	0 to V_{CC}	V	
V_O	Output Voltage	0 to V_{CC}	V	
T_{op}	Operating Temperature: M54HC Series M74HC Series	-55 to +125 -40 to +85	°C °C	
t_r, t_f	Input Rise and Fall Time	$V_{CC} = 2\text{ V}$ $V_{CC} = 4.5\text{ V}$ $V_{CC} = 6\text{ V}$	0 to 1000 0 to 500 0 to 400	ns

DC SPECIFICATIONS

Symbol	Parameter	Test Conditions		Value						Unit		
				$T_A = 25\text{ °C}$ 54HC and 74HC			$-40\text{ to }85\text{ °C}$ 74HC		$-55\text{ to }125\text{ °C}$ 54HC			
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.	
V_{IH}	High Level Input Voltage	V_{CC} (V)		1.5			1.5		1.5		V	
				3.15			3.15		3.15			
				4.2			4.2		4.2			
V_{IL}	Low Level Input Voltage	V_{CC} (V)				0.5		0.5		0.5	V	
						1.35		1.35		1.35		
						1.8		1.8		1.8		
V_{OH}	High Level Output Voltage	V_{CC} (V)	$V_I = V_{IH}$ or V_{IL}	$I_O = -20\text{ }\mu\text{A}$	1.9	2.0		1.9		1.9		V
					4.4	4.5		4.4		4.4		
					5.9	6.0		5.9		5.9		
					4.18	4.31		4.13		4.10		
					5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output Voltage	V_{CC} (V)	$V_I = V_{IH}$ or V_{IL}	$I_O = 20\text{ }\mu\text{A}$		0.0	0.1		0.1		0.1	V
						0.0	0.1		0.1		0.1	
						0.0	0.1		0.1		0.1	
						0.17	0.26		0.33		0.40	
						0.18	0.26		0.33		0.40	
I_I	Input Leakage Current	6.0	$V_I = V_{CC}$ or GND			± 0.1		± 1		± 1	μA	
I_{OZ}	3 State Output Off State Current	6.0	$V_I = V_{IH}$ or V_{IL} $V_O = V_{CC}$ or GND			± 0.5		± 5		± 10	μA	
I_{CC}	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND			4		40		80	μA	

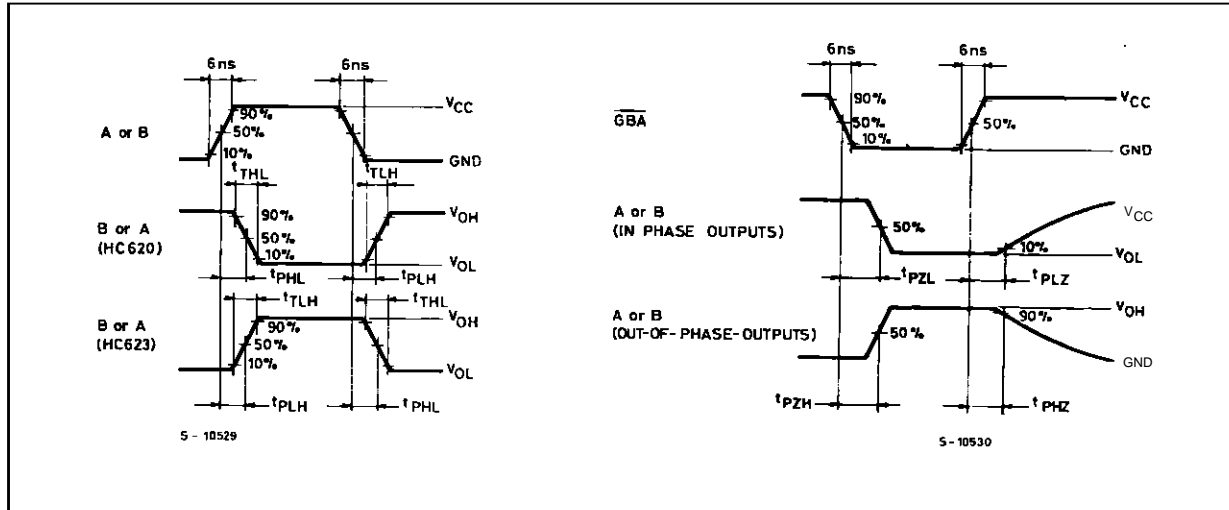
AC ELECTRICAL CHARACTERISTICS ($C_L = 50$ pF, Input $t_r = t_f = 6$ ns)

Symbol	Parameter	Test Conditions			Value						Unit	
		V_{CC} (V)	C_L (pF)		$T_A = 25\text{ }^\circ\text{C}$ 54HC and 74HC			$-40\text{ to }85\text{ }^\circ\text{C}$ 74HC		$-55\text{ to }125\text{ }^\circ\text{C}$ 54HC		
					Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t_{TLH} t_{THL}	Output Transition Time	2.0 4.5 6.0	50		25 7 6	60 12 10		75 15 13		90 18 15	ns	
t_{PLH} t_{PHL}	Propagation Delay Time (for HC620)	2.0 4.5 6.0 2.0 4.5 6.0	50 150		41 12 10 55 16 14	100 20 17 130 26 22		125 25 21 165 33 28		150 30 26 195 39 33	ns ns	
t_{PLH} t_{PHL}	Propagation Delay Time (for HC623)	2.0 4.5 6.0 2.0 4.5 6.0	50 150		38 12 10 51 16 14	85 17 14 130 26 22		105 21 18 165 33 28		130 26 22 195 39 33	ns ns	
t_{PZL} t_{PZH}	Output Enable Time	2.0 4.5 6.0 2.0 4.5 0	50 150	$R_L = 1\text{ K}\Omega$ $R_L = 1\text{ K}\Omega$	57 19 16 69 23 20	150 30 26 180 36 31		190 38 32 225 45 38		225 45 38 270 54 46	ns ns	
t_{PLZ} t_{PHZ}	Output Disable Time	2.0 4.5 6.0	50	$R_L = 1\text{ K}\Omega$	43 18 15	125 25 21		155 31 26		190 38 32	ns	
C_{IN}	Input Capacitance				5	10		10		10	pF	
$C_{PD} (*)$	Power Dissipation Capacitance			for HC620 for HC623	32 34						pF	

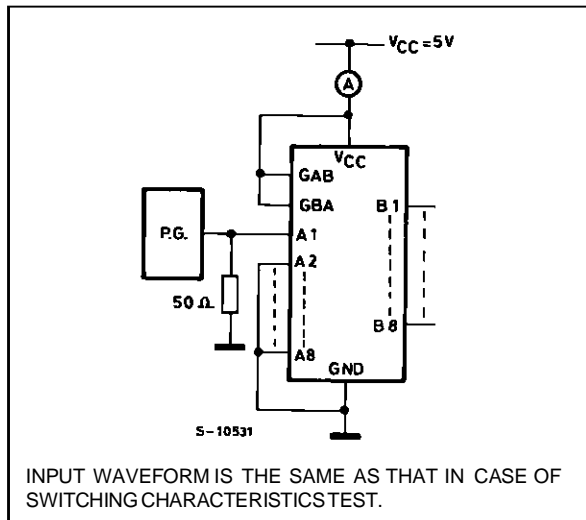
C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

M54/M74HC620/623

SWITCHING CHARACTERISTICS TEST WAVEFORM



TEST CIRCUIT I_{CC} (Opr.)



C_{PD} CALCULATION

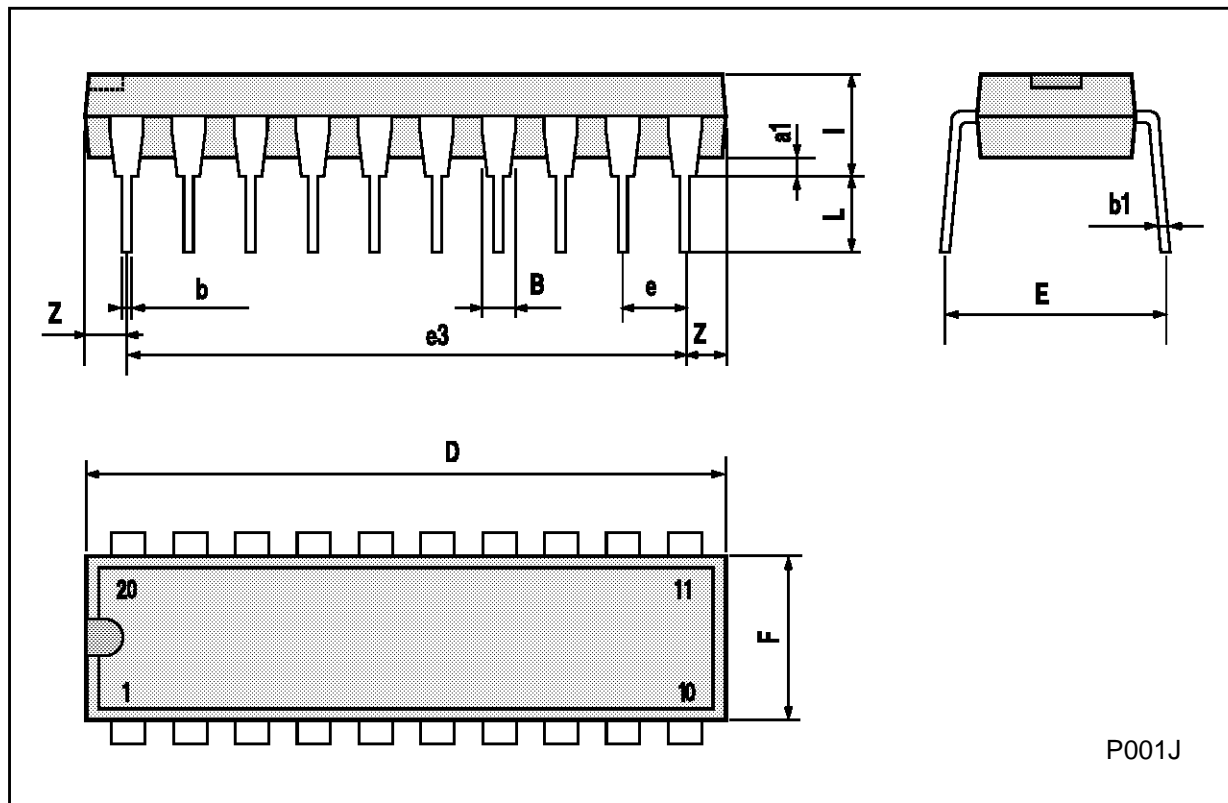
C_{PD} is to be calculated with the following formula by using the measured value of I_{CC} (Opr.) in the test circuit opposite.

$$C_{PD} = \frac{I_{CC} (Opr.)}{f_{IN} \times V_{CC}}$$

In determining the typical value of C_{PD}, a relatively high frequency of 1 MHz was applied to f_{IN}, in order to eliminate any error caused by the quiescent supply current.

Plastic DIP20 (0.25) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.254			0.010		
B	1.39		1.65	0.055		0.065
b		0.45			0.018	
b1		0.25			0.010	
D			25.4			1.000
E		8.5			0.335	
e		2.54			0.100	
e3		22.86			0.900	
F			7.1			0.280
l			3.93			0.155
L		3.3			0.130	
Z			1.34			0.053

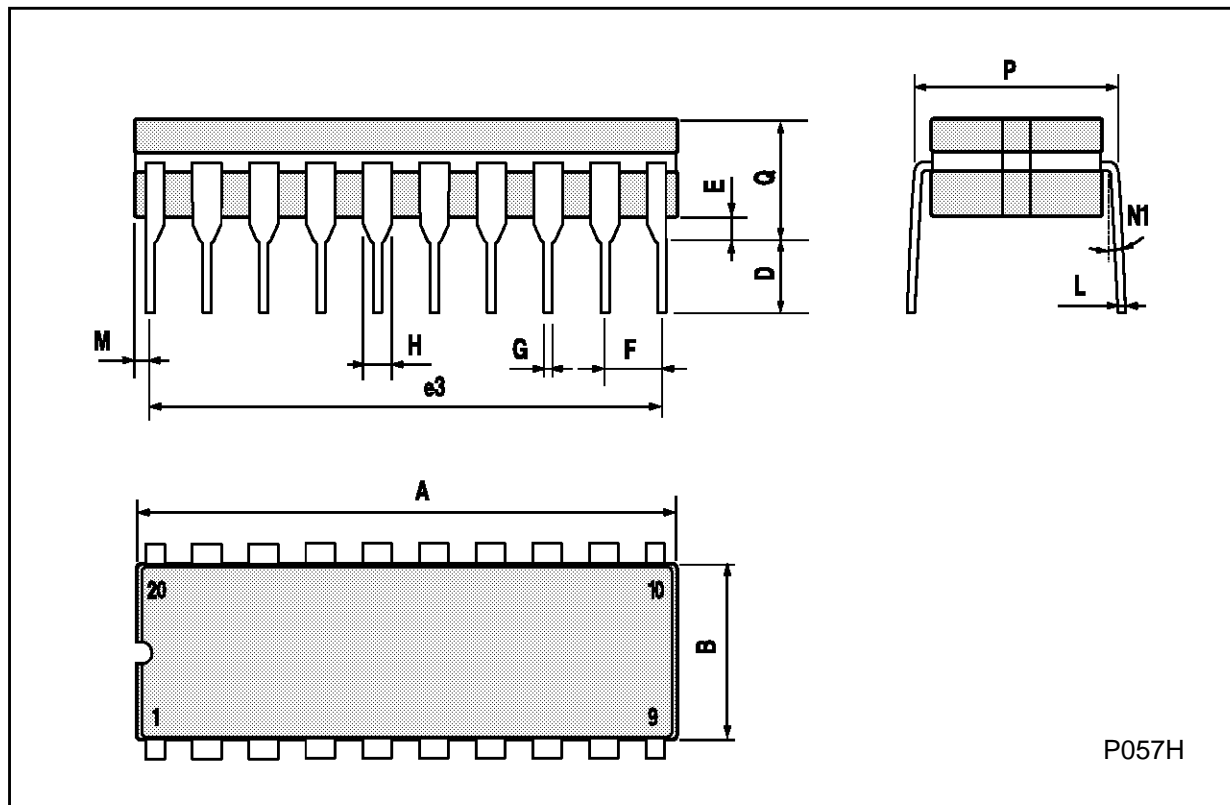


P001J

M54/M74HC620/623

Ceramic DIP20 MECHANICAL DATA

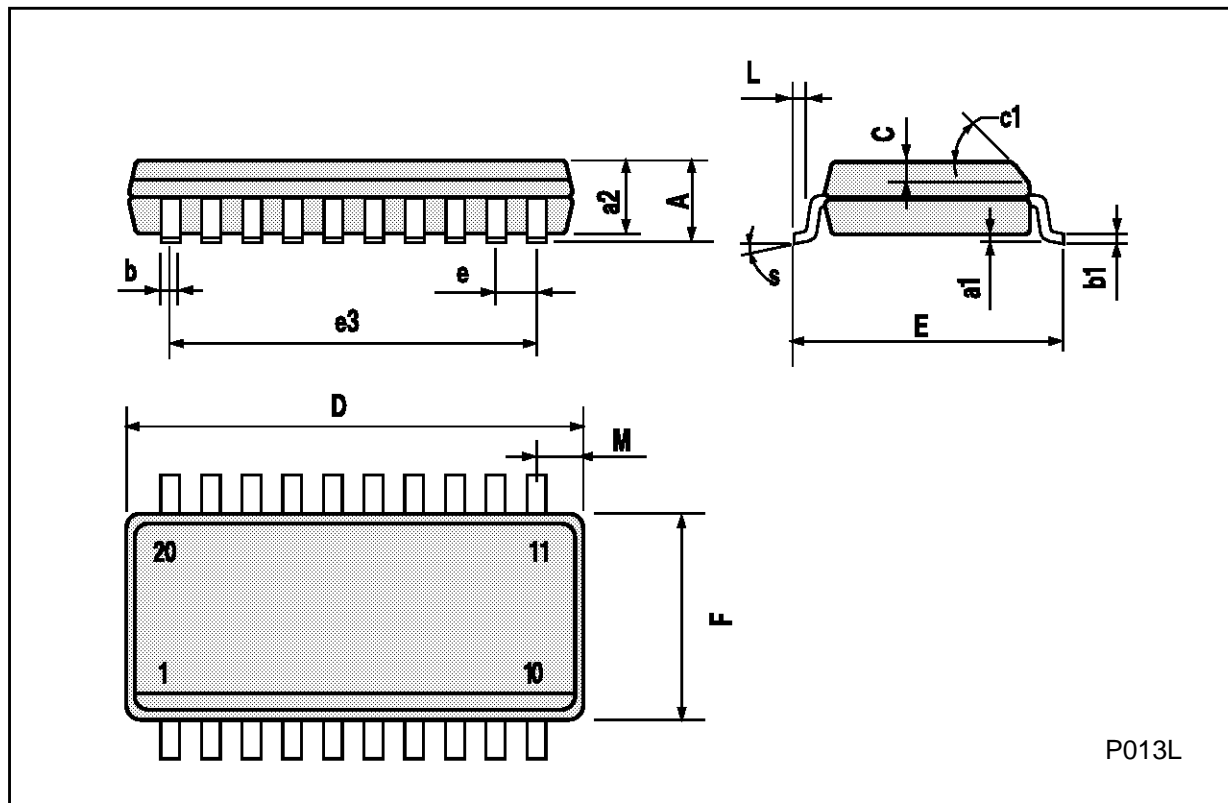
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			25			0.984
B			7.8			0.307
D		3.3			0.130	
E	0.5		1.78	0.020		0.070
e3		22.86			0.900	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
I	1.27		1.52	0.050		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N1	4° (min.), 15° (max.)					
P	7.9		8.13	0.311		0.320
Q			5.71			0.225



P057H

SO20 MECHANICAL DATA

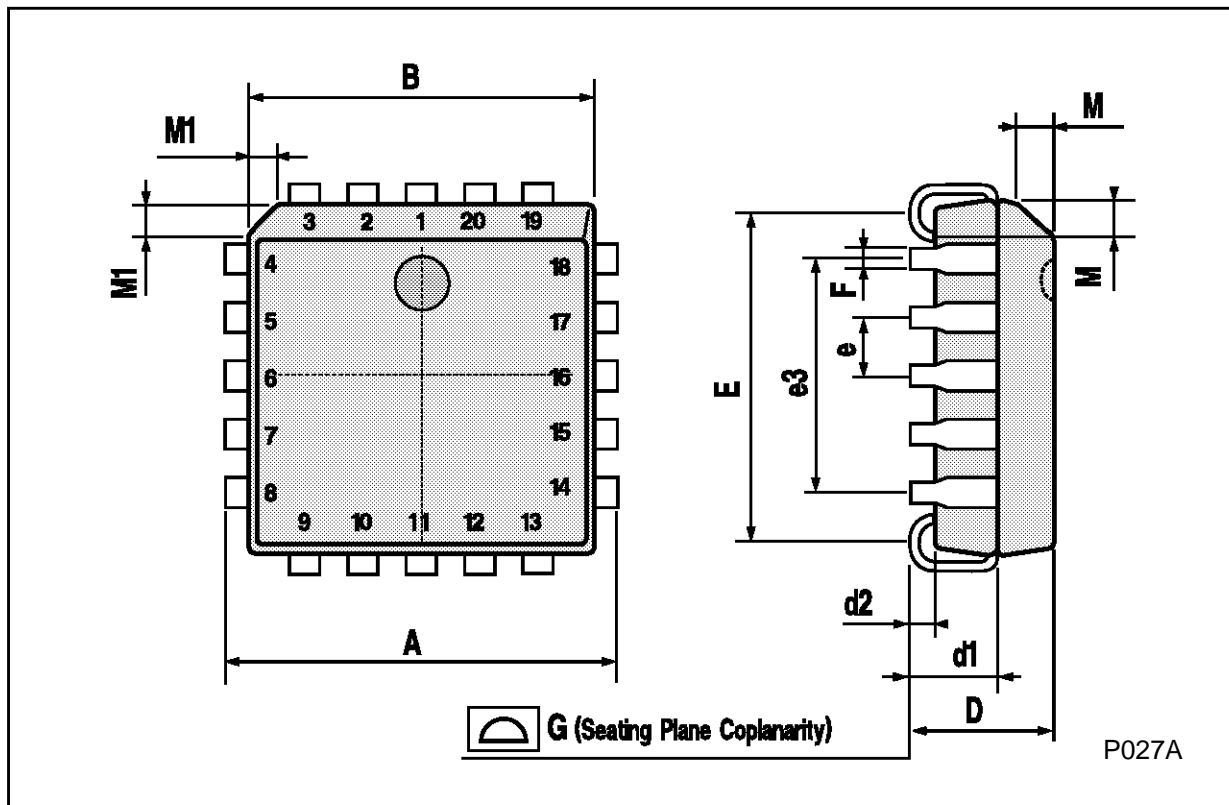
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.10		0.20	0.004		0.007
a2			2.45			0.096
b	0.35		0.49	0.013		0.019
b1	0.23		0.32	0.009		0.012
C		0.50			0.020	
c1	45° (typ.)					
D	12.60		13.00	0.496		0.512
E	10.00		10.65	0.393		0.419
e		1.27			0.050	
e3		11.43			0.450	
F	7.40		7.60	0.291		0.299
L	0.50		1.27	0.19		0.050
M			0.75			0.029
S	8° (max.)					



P013L

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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